

MA3X730

Silicon epitaxial planar type

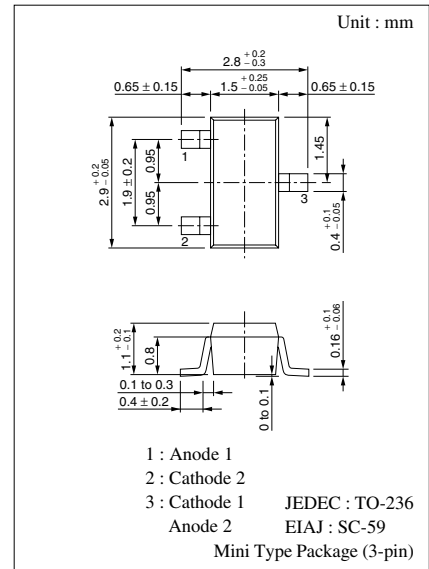
For UHF mixer

■ Features

- Two MA2X707s are contained in the (Mini (3-pin) type)
- Large conversion gain (GC)
- Small forward voltage V_F
- Optimum for the UHF band mixer

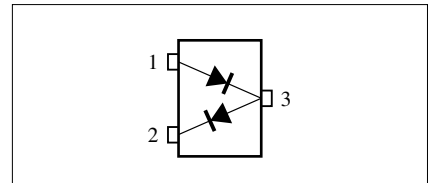
■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Forward voltage (DC)	V_F	0.5	V
Reverse voltage (DC)	V_R	5	V
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$



Marking Symbol: M2X

Internal Connection



■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward current (DC)	I_F	$V_F = 0.5 \text{ V}$	35		100	mA
Reverse current (DC)	I_R	$V_R = 5 \text{ V}$			35	μA
Forward voltage (DC)	V_F	$I_F = 2 \text{ mA}$		0.25		V
Reverse breakdown voltage (DC)	$V_{(BR)R}$	$I_R = 1 \text{ mA}$	5			V
Terminal capacitance	C_t	$V_R = 0.5 \text{ V}, f = 1 \text{ MHz}$	0.65	0.85	1.05	pF
Conversion gain ^{*1,2}	GC	$R_F = 890 \text{ MHz}, L_O = 935 \text{ MHz}$ $I_F = 45 \text{ MHz}$	-7	-5		dB
Static breakdown strength		$C = 100 \text{ pF}$, Breakdown judgment point $I_R \geq 35 \mu\text{A}$	100	200		V

Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment

2. Rated input/output frequency: 935 MHz

3. Noise index is 8.5 dB

4. Each characteristic is a standard for individual diodes

5. *1 : Judgement is to be made per each chip lot. Sampling of LTPD = 20% and $n = 11$ is guaranteed.

*2 : Set min. GC = -7 dB. Out-spec products, if any, this specification would be reviewed

